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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	31775
Number of Logic Elements/Cells	406720
Total RAM Bits	29306880
Number of I/O	400
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	676-BBGA, FCBGA
Supplier Device Package	676-FCBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k410t-2ffg676c

Table 3: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
$R_{IN_TERM}^{(4)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40) for commercial (C), industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50) for commercial (C), industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60) for commercial (C), industrial (I), and extended (E) temperature devices	44	60	83	Ω
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{CCO}/2$ level.

Table 4: Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks⁽¹⁾

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
$V_{CCO} + 0.40$	100	–0.40	100
$V_{CCO} + 0.45$	100	–0.45	61.7
$V_{CCO} + 0.50$	100	–0.50	25.8
$V_{CCO} + 0.55$	100	–0.55	11.0
$V_{CCO} + 0.60$	46.6	–0.60	4.77
$V_{CCO} + 0.65$	21.2	–0.65	2.10
$V_{CCO} + 0.70$	9.75	–0.70	0.94
$V_{CCO} + 0.75$	4.55	–0.75	0.43
$V_{CCO} + 0.80$	2.15	–0.80	0.20
$V_{CCO} + 0.85$	1.02	–0.85	0.09
$V_{CCO} + 0.90$	0.49	–0.90	0.04
$V_{CCO} + 0.95$	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks⁽¹⁾⁽²⁾

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
$V_{CCO} + 0.40$	100	–0.40	100
$V_{CCO} + 0.45$	100	–0.45	100
$V_{CCO} + 0.50$	100	–0.50	100
$V_{CCO} + 0.55$	100	–0.55	100
$V_{CCO} + 0.60$	50.0	–0.60	50.0
$V_{CCO} + 0.65$	50.0	–0.65	50.0
$V_{CCO} + 0.70$	47.0	–0.70	50.0
$V_{CCO} + 0.75$	21.2	–0.75	50.0

Table 6: Typical Quiescent Supply Current (Cont'd)

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I _{CCBRAMQ}	Quiescent V _{CCBRAM} supply current	XC7K70T	6	6	6	6	mA
		XC7K160T	14	14	14	14	mA
		XC7K325T	19	19	19	19	mA
		XC7K355T	31	31	31	31	mA
		XC7K410T	34	34	34	34	mA
		XC7K420T	41	41	41	41	mA
		XC7K480T	41	41	41	41	mA

Notes:

- Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
- Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
- Use the XPower™ Estimator (XPE) spreadsheet tool (download at <http://www.xilinx.com/power>) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than T_{VCCO2VCCAUX} for each power-on/off cycle to maintain device reliability levels.
- The T_{VCCO2VCCAUX} time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX transceivers is V_{CCINT}, V_{MGTAVCC}, V_{MGTAVTT} OR V_{MGTAVCC}, V_{CCINT}, V_{MGTAVTT}. There is no recommended sequencing for V_{MGTVCCAUX}. Both V_{MGTAVCC} and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from V_{MGTAVTT} can be higher than specifications during power-up and power-down.

- When V_{MGTAVTT} is powered before V_{MGTAVCC} and V_{MGTAVTT} - V_{MGTAVCC} > 150 mV and V_{MGTAVCC} < 0.7V, the V_{MGTAVTT} current draw can increase by 460 mA per transceiver during V_{MGTAVCC} ramp up. The duration of the current draw can be up to 0.3 x T_{MGTAVCC} (ramp time from GND to 90% of V_{MGTAVCC}). The reverse is true for power-down.
- When V_{MGTAVTT} is powered before V_{CCINT} and V_{MGTAVTT} - V_{CCINT} > 150 mV and V_{CCINT} < 0.7V, the V_{MGTAVTT} current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 7 shows the minimum current, in addition to I_{CCQ} , that are required by Kintex-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: Power-On Current for Kintex-7 Devices

Device	$I_{CCINTMIN}$ Typ ⁽¹⁾	$I_{CCAUXMIN}$ Typ ⁽¹⁾	I_{CCOMIN} Typ ⁽¹⁾	I_{CCAUX_IOMIN} Typ ⁽¹⁾	$I_{CCBRAMMIN}$ Typ ⁽¹⁾	Units
XC7K70T	$I_{CCINTQ} + 450$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 40$	mA
XC7K160T	$I_{CCINTQ} + 550$	$I_{CCAUXQ} + 50$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 40$	mA
XC7K325T	$I_{CCINTQ} + 600$	$I_{CCAUXQ} + 80$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 40$	mA
XC7K355T	$I_{CCINTQ} + 1450$	$I_{CCAUXQ} + 109$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 81$	mA
XC7K410T	$I_{CCINTQ} + 1500$	$I_{CCAUXQ} + 125$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 90$	mA
XC7K420T	$I_{CCINTQ} + 2200$	$I_{CCAUXQ} + 180$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 108$	mA
XC7K480T	$I_{CCINTQ} + 2200$	$I_{CCAUXQ} + 180$	$I_{CCOQ} + 40$ mA per bank	$I_{CCOAXIOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 108$	mA

Notes:

- Typical values are specified at nominal voltage, 25°C.
- Use the XPower Estimator (XPE) spreadsheet tool (download at <http://www.xilinx.com/power>) to calculate maximum power-on currents.

Table 8: Power Supply Ramp Time

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100^{\circ}C^{(1)}$	–	500	ms
		$T_J = 85^{\circ}C^{(1)}$	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

- Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: SelectIO DC Input and Output Levels (1)(2)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8	-8
HSTL_I_12	-0.300	$V_{REF} - 0.080$	$V_{REF} + 0.080$	$V_{CCO} + 0.300$	25% V_{CCO}	75% V_{CCO}	6.3	-6.3
HSTL_I_18	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8	-8
HSTL_II	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16	-16
HSTL_II_18	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16	-16
HSUL_12	-0.300	$V_{REF} - 0.130$	$V_{REF} + 0.130$	$V_{CCO} + 0.300$	20% V_{CCO}	80% V_{CCO}	0.1	-0.1
LVC MOS12	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 3	Note 3
LVC MOS15, LVDCI_15	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVC MOS18, LVDCI_18	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.450	$V_{CCO} - 0.450$	Note 5	Note 5
LVC MOS25	-0.300	0.700	1.700	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 6	Note 6
LVC MOS33	-0.300	0.800	2.000	3.450	0.400	$V_{CCO} - 0.400$	Note 6	Note 6
LV TTL	-0.300	0.800	2.000	3.450	0.400	2.400	Note 7	Note 7
MOBILE_DDR	-0.300	20% V_{CCO}	80% V_{CCO}	$V_{CCO} + 0.300$	10% V_{CCO}	90% V_{CCO}	0.1	-0.1
PCI33_3	-0.500	30% V_{CCO}	50% V_{CCO}	$V_{CCO} + 0.500$	10% V_{CCO}	90% V_{CCO}	1.5	-0.5
SSTL12	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	14.25	-14.25
SSTL135	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	13.0	-13.0
SSTL135_R	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	8.9	-8.9
SSTL15	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	13.0	-13.0
SSTL15_R	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	8.9	-8.9
SSTL18_I	-0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.470$	$V_{CCO}/2 + 0.470$	8	-8
SSTL18_II	-0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.600$	$V_{CCO}/2 + 0.600$	13.4	-13.4

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks and 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, or 16 mA
7. Supported drive strengths of 4, 8, 12, 16, or 24 mA
8. For detailed interface specific DC voltage levels, see [UG471: 7 Series FPGAs SelectIO Resources User Guide](#).

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

[Table 15](#) lists the production released Kintex-7 device, speed grade, and the minimum corresponding supported speed specification version and ISE software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 15: Kintex-7 Device Production Software and Speed Specification Release

Device	Speed Grade Designations			
	1.0V			0.9V
	-3	-2/-2L	-1	-2L
XC7K70T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K160T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K325T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K355T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K410T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K420T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K480T	ISE 14.2 v1.06			ISE 14.3 v1.06

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Kintex-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the [AC Switching Characteristics, page 11](#). In each table, the I/O bank type is either High Performance (HP) or High Range (HR).

Table 16: Networking Applications Interface Performances

Description	I/O Bank Type	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	HR	710	710	625	625	Mb/s
	HP	710	710	625	625	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	HR	1250	1250	950	950	Mb/s
	HP	1600	1400	1250	1250	Mb/s
SDR LVDS receiver (SFI-4.1) ⁽¹⁾	HR	710	710	625	625	Mb/s
	HP	710	710	625	625	Mb/s
DDR LVDS receiver (SFI-4.2) ⁽¹⁾	HR	1250	1250	950	950	Mb/s
	HP	1600	1400	1250	1250	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 17: Maximum Physical Interface (PHY) Rate for Memory Interfaces (FFG Packages)⁽¹⁾⁽²⁾

Memory Standard	I/O Bank Type	V _{CCAUX_IO}	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	2.0V	1866	1866	1600	1333	Mb/s
	HP	1.8V	1600	1333	1066	1066	Mb/s
	HR	N/A	1066	1066	800	800	Mb/s
DDR3L	HP	2.0V	1600	1600	1333	1066	Mb/s
	HP	1.8V	1333	1066	800	800	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V	800	800	800	800	Mb/s
	HR	N/A	800	800	800	800	Mb/s
RLDRAM III ⁽³⁾	HP	2.0V	800	667	667	533	MHz
	HP	1.8V	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	2.0V	1066	1066	800	800	Mb/s
	HP	1.8V	1066	1066	800	800	Mb/s
	HR	N/A	1066	1066	800	800	Mb/s
DDR3L	HP	2.0V	1066	1066	800	800	Mb/s
	HP	1.8V	1066	1066	800	800	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V					
	HR	N/A					
QDR II+ ⁽⁴⁾	HP	2.0V	550	500	450	450	MHz
	HP	1.8V					
	HR	N/A					
RLDRAM II	HP	2.0V	533	500	450	450	MHz
	HP	1.8V					
	HR	N/A					
LPDDR2 ⁽³⁾	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see [UG586](#), 7 Series FPGAs Memory Interface Solutions User Guide.
2. When using the internal V_{REF} the maximum data rate is 800 Mb/s (400 MHz).
3. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
4. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

Table 18: Maximum Physical Interface (PHY) Rate for Memory Interfaces (FBG Packages)⁽¹⁾⁽²⁾

Memory Standard	I/O Bank Type	V _{CCAUX_IO} ⁽³⁾	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	N/A	1333	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
RLDRAM III ⁽⁴⁾	HP	N/A	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	N/A	1066	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
QDR II+ ⁽⁵⁾	HP	N/A	550	500	450	450	MHz
	HR	N/A	450	400	350	350	MHz
RLDRAM II	HP	N/A	533	500	450	450	MHz
	HR	N/A					
LPDDR2 ⁽⁴⁾	HP	N/A	667	667	667	667	Mb/s
	HR	N/A	667	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see [UG586](#), *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF} the maximum data rate is 800 Mb/s (400 MHz).
3. FBG packages do not have separate V_{CCAUX_IO} supply pins to adjust the pre-driver voltage of the HP I/O banks.
4. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
5. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: IOB 3-state Output Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

Table 23: OLOGIC Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T _{ODCK} /T _{OCKD}	D1/D2 pins Setup/Hold with respect to CLK	0.45/−0.13	0.50/−0.13	0.58/−0.13	0.79/−0.18	ns
T _{OOCECK} /T _{OCKOCE}	OCE pin Setup/Hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	0.35/−0.10	ns
T _{OSRCK} /T _{OCKSR}	SR pin Setup/Hold with respect to CLK	0.32/0.18	0.38/0.18	0.70/0.18	0.62/−0.04	ns
T _{OTCK} /T _{OCKT}	T1/T2 pins Setup/Hold with respect to CLK	0.49/−0.16	0.56/−0.16	0.68/−0.16	0.67/−0.18	ns
T _{OTCECK} /T _{OCKTCE}	TCE pin Setup/Hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	0.31/−0.10	ns
Combinatorial						
T _{ODQ}	D1 to OQ out or T1 to TQ out	0.73	0.81	0.97	1.18	ns
Sequential Delays						
T _{OCKQ}	CLK to OQ/TQ out	0.41	0.43	0.49	0.63	ns
T _{RQ_OLOGICE2}	SR pin to OQ/TQ out (HP I/O banks only)	0.63	0.70	0.83	1.12	ns
T _{GSRQ_OLOGICE2}	Global Set/Reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	11.39	ns
T _{RQ_OLOGICE3}	SR pin to OQ/TQ out (HR I/O banks only)	0.63	0.70	0.83	1.12	ns
T _{GSRQ_OLOGICE3}	Global Set/Reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	11.39	ns
Set/Reset						
T _{RPW_OLOGICE2}	Minimum Pulse Width, SR inputs (HP I/O banks only)	0.54	0.54	0.63	0.68	ns, Min
T _{RPW_OLOGICE3}	Minimum Pulse Width, SR inputs (HR I/O banks only)	0.54	0.54	0.63	0.68	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 24: ISERDES Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
T _{ISCK_BITSLIP} / T _{ISCKC_BITSLIP}	BITSLIP pin Setup/Hold with respect to CLKDIV	0.01/0.12	0.02/0.13	0.02/0.15	0.02/0.21	ns
T _{ISCK_CE} / T _{ISCKC_CE} ⁽²⁾	CE pin Setup/Hold with respect to CLK (for CE1)	0.39/−0.02	0.44/−0.02	0.63/−0.02	0.51/−0.22	ns
T _{ISCK_CE2} / T _{ISCKC_CE2} ⁽²⁾	CE pin Setup/Hold with respect to CLKDIV (for CE2)	−0.12/0.29	−0.12/0.31	−0.12/0.35	−0.17/0.40	ns
Setup/Hold for Data Lines						
T _{ISDCK_D} /T _{ISCKD_D}	D pin Setup/Hold with respect to CLK	−0.02/0.11	−0.02/0.12	−0.02/0.15	−0.04/0.19	ns
T _{ISDCK_DDLY} / T _{ISCKD_DDLY}	DDLY pin Setup/Hold with respect to CLK (using IDELAY) ⁽¹⁾	−0.02/0.11	−0.02/0.12	−0.02/0.15	−0.03/0.19	ns
T _{ISDCK_D_DDR} / T _{ISCKD_D_DDR}	D pin Setup/Hold with respect to CLK at DDR mode	−0.02/0.11	−0.02/0.12	−0.02/0.15	−0.04/0.19	ns
T _{ISDCK_DDLY_DDR} / T _{ISCKD_DDLY_DDR}	D pin Setup/Hold with respect to CLK at DDR mode (using IDELAY) ⁽¹⁾	0.11/0.11	0.12/0.12	0.15/0.15	0.19/0.19	ns
Sequential Delays						
T _{ISCKO_Q}	CLKDIV to out at Q pin	0.46	0.47	0.58	0.67	ns
Propagation Delays						
T _{ISDO_DO}	D input to DO output pin	0.09	0.10	0.12	0.14	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCK_CE2} and T_{ISCK_CE2} are reported as T_{ISCK_CE}/T_{ISCK_CE} in TRACE report.

Input/Output Delay Switching Characteristics

Table 26: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IDELAYCTRL						
T _{DLYCCO_RDY}	Reset to Ready for IDELAYCTRL	3.22	3.22	3.22	3.22	μs
F _{IDELAYCTRL_REF}	Attribute REFCLK frequency = 200.00 ⁽¹⁾	200.00	200.00	200.00	200.00	MHz
	Attribute REFCLK frequency = 300.00 ⁽¹⁾	300.00	300.00	N/A	N/A	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
T _{IDELAYCTRL_RPW}	Minimum Reset pulse width	52.00	52.00	52.00	52.00	ns
IDELAY/ODELAY						
T _{IDELAYRESOLUTION}	IDELAY/ODELAY chain delay resolution	1/(32 x 2 x F _{REF})				ps
T _{IDELAYPAT_JIT} and T _{ODELAYPAT_JIT}	Pattern dependent period jitter in delay chain for clock pattern. ⁽²⁾	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23) ⁽³⁾	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23) ⁽⁴⁾	±9	±9	±9	±9	ps per tap
T _{IDELAY_CLK_MAX} / T _{ODELAY_CLK_MAX}	Maximum frequency of CLK input to IDELAY/ODELAY	800.00	800.00	710.00	710.00	MHz
T _{IDCCK_CE} / T _{IDCKC_CE}	CE pin Setup/Hold with respect to C for IDELAY	0.11/0.10	0.14/0.12	0.18/0.14	0.14/0.16	ns
T _{ODCCK_CE} / T _{ODCKC_CE}	CE pin Setup/Hold with respect to C for ODELAY	0.14/0.03	0.16/0.04	0.19/0.05	0.28/0.06	ns
T _{IDCCK_INC} / T _{IDCKC_INC}	INC pin Setup/Hold with respect to C for IDELAY	0.10/0.14	0.12/0.16	0.14/0.20	0.10/0.23	ns
T _{ODCCK_INC} / T _{ODCKC_INC}	INC pin Setup/Hold with respect to C for ODELAY	0.10/0.07	0.12/0.08	0.13/0.09	0.19/0.16	ns
T _{IDCCK_RST} / T _{IDCKC_RST}	RST pin Setup/Hold with respect to C for IDELAY	0.13/0.08	0.14/0.10	0.16/0.12	0.22/0.19	ns
T _{ODCCK_RST} / T _{ODCKC_RST}	RST pin Setup/Hold with respect to C for ODELAY	0.16/0.04	0.19/0.06	0.24/0.08	0.32/0.11	ns
T _{IDDO_IDATAIN}	Propagation delay through IDELAY	Note 5	Note 5	Note 5	Note 5	ps
T _{ODDO_ODATAIN}	Propagation delay through ODELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE.
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY/ODELAY tap setting. See TRACE report for actual values.

Table 27: IO_FIFO Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T _{OFFCKO_DO}	RDCLK to Q outputs	0.51	0.56	0.63	0.81	ns
T _{CKO_FLAGS}	Clock to IO_FIFO Flags	0.59	0.62	0.81	0.77	ns
Setup/Hold						
T _{CCK_D} /T _{CKC_D}	D inputs to WRCLK	0.43/−0.01	0.47/−0.01	0.53/−0.01	0.76/−0.05	ns
T _{IFFCKC_WREN} /T _{IFFCKC_WREN}	WREN to WRCLK	0.39/−0.01	0.43/−0.01	0.50/−0.01	0.70/−0.05	ns
T _{OFFCKC_RDEN} /T _{OFFCKC_RDEN}	RDEN to RDCLK	0.49/0.01	0.53/0.02	0.61/0.02	0.79/−0.02	ns
Minimum Pulse Width						
T _{PWH_IO_FIFO}	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
T _{PWL_IO_FIFO}	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
Maximum Frequency						
F _{MAX}	RDCLK and WRCLK	533.05	470.37	400.00	333.33	MHz

MMCM Switching Characteristics

Table 38: MMCM Specification

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
MMCM_F _{INMAX}	Maximum Input Clock Frequency	1066.00	933.00	800.00	800.00	MHz
MMCM_F _{INMIN}	Minimum Input Clock Frequency	10.00	10.00	10.00	10.00	MHz
MMCM_F _{INJITTER}	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
MMCM_F _{INDUTY}	Allowable Input Duty Cycle: 10—49 MHz	25.00	25.00	25.00	25.00	%
	Allowable Input Duty Cycle: 50—199 MHz	30.00	30.00	30.00	30.00	%
	Allowable Input Duty Cycle: 200—399 MHz	35.00	35.00	35.00	35.00	%
	Allowable Input Duty Cycle: 400—499 MHz	40.00	40.00	40.00	40.00	%
	Allowable Input Duty Cycle: >500 MHz	45.00	45.00	45.00	45.00	%
MMCM_F _{MIN_PSCLK}	Minimum Dynamic Phase Shift Clock Frequency	0.01	0.01	0.01	0.01	MHz
MMCM_F _{MAX_PSCLK}	Maximum Dynamic Phase Shift Clock Frequency	550.00	500.00	450.00	450.00	MHz
MMCM_F _{VCOMIN}	Minimum MMCM VCO Frequency	600.00	600.00	600.00	600.00	MHz
MMCM_F _{VCOMAX}	Maximum MMCM VCO Frequency	1600.00	1440.00	1200.00	1200.00	MHz
MMCM_F _{BANDWIDTH}	Low MMCM Bandwidth at Typical ⁽¹⁾	1.00	1.00	1.00	1.00	MHz
	High MMCM Bandwidth at Typical ⁽¹⁾	4.00	4.00	4.00	4.00	MHz
MMCM_T _{STATPHAOFFSET}	Static Phase Offset of the MMCM Outputs ⁽²⁾	0.12	0.12	0.12	0.12	ns
MMCM_T _{OUTJITTER}	MMCM Output Jitter	Note 3				
MMCM_T _{OUTDUTY}	MMCM Output Clock Duty Cycle Precision ⁽⁴⁾	0.20	0.20	0.20	0.25	ns
MMCM_T _{LOCKMAX}	MMCM Maximum Lock Time	100.00	100.00	100.00	100.00	μs
MMCM_F _{OUTMAX}	MMCM Maximum Output Frequency	1066.00	933.00	800.00	800.00	MHz
MMCM_F _{OUTMIN}	MMCM Minimum Output Frequency ⁽⁵⁾⁽⁶⁾	4.69	4.69	4.69	4.69	MHz
MMCM_T _{EXTFDVAR}	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				
MMCM_RST _{MINPULSE}	Minimum Reset Pulse Width	5.00	5.00	5.00	5.00	ns
MMCM_F _{PFDMAX}	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized	550.00	500.00	450.00	450.00	MHz
	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	300.00	300.00	300.00	300.00	MHz
MMCM_F _{PFDMIN}	Minimum Frequency at the Phase Frequency Detector	10.00	10.00	10.00	10.00	MHz
MMCM_T _{FBDELAY}	Maximum Delay in the Feedback Path	3 ns Max or one CLKIN cycle				
MMCM Switching Characteristics Setup and Hold						
T _{MMCMDCK_PSEN} / T _{MMCMCKD_PSEN}	Setup and Hold of Phase Shift Enable	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
T _{MMCMDCK_PSINCDEC} / T _{MMCMCKD_PSINCDEC}	Setup and Hold of Phase Shift Increment/Decrement	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
T _{MMCMCKO_PSDONE}	Phase Shift Clock-to-Out of PSDONE	0.59	0.68	0.81	0.78	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK						
T _{MMCMDCK_DADDR} / T _{MMCMCKD_DADDR}	DADDR Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
T _{MMCMDCK_DI} / T _{MMCMCKD_DI}	DI Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min

Device Pin-to-Pin Input Parameter Guidelines

All devices are 100% functionally tested. Values are expressed in nanoseconds unless otherwise noted.

Table 45: Global Clock Input Setup and Hold Without MMCM/PLL with ZHOLD_DELAY on HR I/O Banks

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard. ⁽¹⁾							
T _{PSFD} / T _{PHFD}	Full Delay (Legacy Delay or Default Delay) Global Clock Input and IFF ⁽²⁾ without MMCM/PLL with ZHOLD_DELAY on HR I/O Banks	XC7K70T	2.83/−0.29	2.95/−0.29	3.15/−0.29	4.96/−0.33	ns
		XC7K160T	3.17/−0.35	3.29/−0.35	3.55/−0.35	5.54/−0.49	ns
		XC7K325T	2.83/−0.06	2.94/−0.06	3.15/−0.06	5.18/−0.14	ns
		XC7K355T	3.26/−0.32	3.41/−0.32	3.67/−0.32	5.84/−0.49	ns
		XC7K410T	3.43/−0.34	3.59/−0.34	3.88/−0.34	6.21/−0.54	ns
		XC7K420T	3.37/−0.27	3.48/−0.27	3.76/−0.27	6.00/−0.52	ns
		XC7K480T	3.37/−0.27	3.48/−0.27	3.76/−0.27	6.00/−0.52	ns

Notes:

- Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage.
- IFF = Input Flip-Flop or Latch
- A Zero "0" Hold Time listing indicates no hold time or a negative hold time.

Table 46: Clock-Capable Clock Input Setup and Hold With MMCM

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard. ⁽¹⁾							
T _{PSMMCMCC} / T _{PHMMCMCC}	No Delay clock-capable clock input and IFF ⁽²⁾ with MMCM	XC7K70T	2.39/−0.22	2.65/−0.22	2.94/−0.22	2.21/−0.44	ns
		XC7K160T	2.49/−0.20	2.77/−0.20	3.07/−0.20	2.38/−0.47	ns
		XC7K325T	2.55/−0.16	2.85/−0.16	3.14/−0.16	2.60/−0.47	ns
		XC7K355T	2.43/−0.16	2.73/−0.16	3.00/−0.16	2.47/−0.43	ns
		XC7K410T	2.55/−0.16	2.84/−0.16	3.14/−0.16	2.58/−0.47	ns
		XC7K420T	2.47/−0.09	2.73/−0.09	3.02/−0.09	2.40/−0.41	ns
		XC7K480T	2.47/−0.09	2.73/−0.09	3.02/−0.09	2.40/−0.41	ns

Notes:

- Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage.
- IFF = Input Flip-Flop or Latch
- Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 47: Clock-Capable Clock Input Setup and Hold With PLL

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
Input Setup and Hold Time Relative to Clock-Capable Clock Input Signal for SSTL15 Standard. ⁽¹⁾							
T _{PSPLLCC} / T _{PHPLLCC}	No Delay clock-capable clock input and IFF ⁽²⁾ with PLL	XC7K70T	2.75/−0.32	3.04/−0.32	3.33/−0.32	2.42/−0.54	ns
		XC7K160T	2.85/−0.31	3.16/−0.31	3.46/−0.31	2.59/−0.56	ns
		XC7K325T	2.91/−0.27	3.24/−0.27	3.54/−0.27	2.80/−0.56	ns
		XC7K355T	2.79/−0.27	3.12/−0.27	3.40/−0.27	2.67/−0.52	ns
		XC7K410T	2.91/−0.27	3.24/−0.27	3.53/−0.27	2.78/−0.56	ns
		XC7K420T	2.83/−0.20	3.12/−0.20	3.41/−0.20	2.61/−0.50	ns
		XC7K480T	2.83/−0.20	3.12/−0.20	3.41/−0.20	2.61/−0.50	ns

Notes:

- Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage.
- IFF = Input Flip-Flop or Latch
- Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 48: Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Input Setup and Hold Time Relative to a Forwarded Clock Input Pin Using BUFIO for SSTL15 Standard.						
T _{PSCS} /T _{PHCS}	Setup/Hold of I/O clock for HR I/O banks	−0.36/1.36	−0.36/1.50	−0.36/1.70	−0.44/1.87	ns
	Setup/Hold of I/O clock for HP I/O banks	−0.34/1.39	−0.34/1.53	−0.34/1.73	−0.44/1.87	ns

Table 49: Sample Window

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T _{SAMP}	Sampling Error at Receiver Pins ⁽¹⁾	0.51	0.56	0.61	0.56	ns
T _{SAMP_BUFIO}	Sampling Error at Receiver Pins using BUFIO ⁽²⁾	0.30	0.35	0.40	0.35	ns

Notes:

- This parameter indicates the total sampling error of the Kintex-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
 - CLK0 MMCM jitter
 - MMCM accuracy (phase offset)
 - MMCM phase shift resolution
These measurements do not include package or clock tree skew.
- This parameter indicates the total sampling error of the Kintex-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

GTX Transceiver Specifications

GTX Transceiver DC Input and Output Levels

Table 51 summarizes the DC output specifications of the GTX transceivers in Kintex-7 FPGAs. Consult [UG476: 7 Series FPGAs GTX/GTH Transceiver User Guide](#) for further details.

Table 51: GTX Transceiver DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage ⁽¹⁾	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage.	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	2	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT} = 1.2V$	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT} = 1.2V$	–	$2/3 V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor ⁽²⁾		–	100	–	nF

Notes:

- The output swing and preemphasis levels are programmable using the attributes discussed in [UG476: 7 Series FPGAs GTX/GTH Transceiver User Guide](#) and can result in values lower than reported in this table.
- Other values can be used as appropriate to conform to specific protocols and standards.

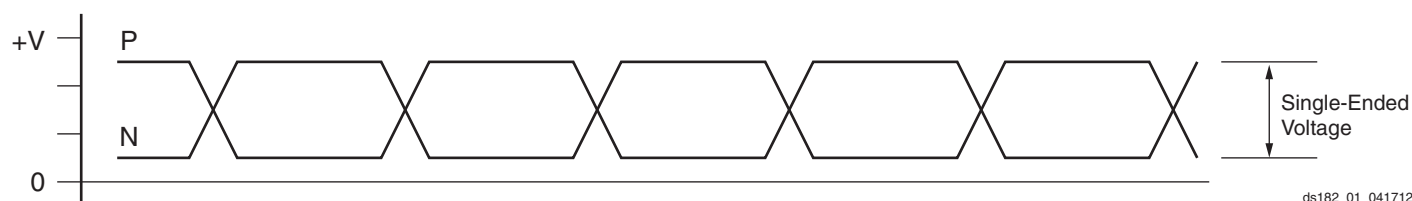


Figure 1: Single-Ended Peak-to-Peak Voltage

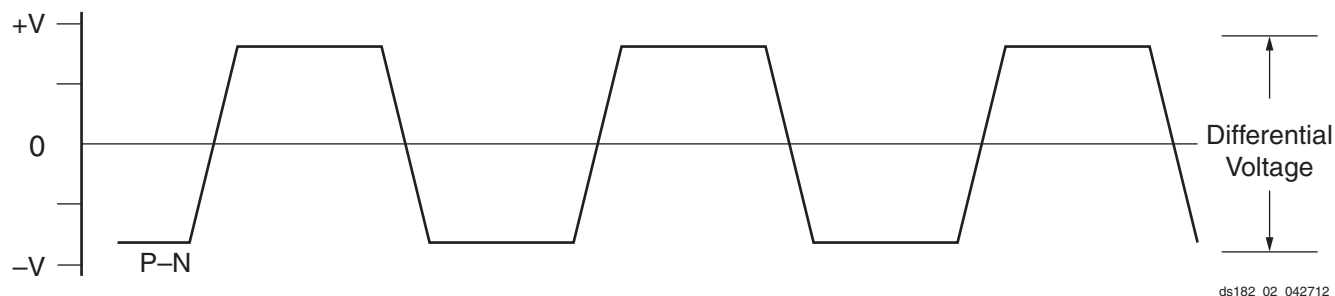


Figure 2: Differential Peak-to-Peak Voltage

Table 52 summarizes the DC specifications of the clock input of the GTX transceiver. Consult [UG476: 7 Series FPGAs GTX/GTH Transceiver User Guide](#) for further details.

Table 52: GTX Transceiver Clock DC Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V _{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R _{IN}	Differential input resistance	–	100	–	Ω
C _{EXT}	Required external AC coupling capacitor	–	100	–	nF

GTX Transceiver Switching Characteristics

Consult [UG476: 7 Series FPGAs GTX/GTH Transceiver User Guide](#) for further information.

Table 53: GTX Transceiver Performance

Symbol	Description	Output Divider	Speed Grade								Units
			1.0V						0.9V		
			-3		-2/-2L		-1 ⁽¹⁾		-2L ⁽²⁾		
			Package Type								
			FF	FB	FF	FB	FF	FB	FF	FB	
F _{GTXMAX} ⁽³⁾	Maximum GTX transceiver data rate		12.5	6.6	10.3125	6.6	8.0	6.6	6.6	6.6	Gb/s
F _{GTXMIN} ⁽³⁾	Minimum GTX transceiver data rate		0.500	0.500	0.500	0.500	0.500	0.500	0.500	0.500	Gb/s
F _{GTXCRANGE}	CPLL line rate range	1	3.2–6.6								Gb/s
		2	1.6–3.3								Gb/s
		4	0.8–1.65								Gb/s
		8	0.5–0.825								Gb/s
		16	N/A								Gb/s
F _{GTXQRANGE1}	QPLL line rate range 1	1	5.93– 8.0	5.93– 6.6	5.93– 8.0	5.93– 6.6	5.93– 8.0	5.93– 6.6	5.93–6.6		Gb/s
		2	2.965–4.0		2.965–4.0		2.965–4.0		2.965–3.3		Gb/s
		4	1.4825–2.0		1.4825–2.0		1.4825–2.0		1.4825–1.65		Gb/s
		8	0.74125–1.0		0.74125–1.0		0.74125–1.0		0.74125–0.825		Gb/s
		16	N/A		N/A		N/A		N/A		Gb/s
F _{GTXQRANGE2}	QPLL line rate range 2 ⁽⁴⁾	1	9.8– 12.5	N/A	9.8– 10.3125	N/A	N/A		N/A		Gb/s
		2	4.9–6.25		4.9–5.15625		N/A		N/A		Gb/s
		4	2.45–3.125		2.45–2.578125		N/A		N/A		Gb/s
		8	1.225–1.5625		1.225–1.2890625		N/A		N/A		Gb/s
		16	0.6125–0.78125		0.6125– 0.64453125		N/A		N/A		Gb/s
F _{GCPLLRANGE}	GTX transceiver CPLL frequency range		1.6–3.3		1.6–3.3		1.6–3.3		1.6–3.3		GHz
F _{GQPLLRange1}	GTX transceiver QPLL frequency range 1		5.93–8.0		5.93–8.0		5.93–8.0		5.93–6.6		GHz

Table 58: GTX Transceiver Transmitter Switching Characteristics (Cont'd)

Symbol	Description	Condition	Min	Typ	Max	Units
TJ _{10.3125}	Total Jitter ⁽²⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.28	UI
DJ _{10.3125}	Deterministic Jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
TJ _{9.953}	Total Jitter ⁽²⁾⁽⁴⁾	9.953 Gb/s	–	–	0.28	UI
DJ _{9.953}	Deterministic Jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
TJ _{9.8}	Total Jitter ⁽²⁾⁽⁴⁾	9.8 Gb/s	–	–	0.28	UI
DJ _{9.8}	Deterministic Jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
TJ _{8.0}	Total Jitter ⁽²⁾⁽⁴⁾	8.0 Gb/s	–	–	0.30	UI
DJ _{8.0}	Deterministic Jitter ⁽²⁾⁽⁴⁾		–	–	0.15	UI
TJ _{6.6_QPLL}	Total Jitter ⁽²⁾⁽⁴⁾	6.6 Gb/s	–	–	0.28	UI
DJ _{6.6_QPLL}	Deterministic Jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
TJ _{6.6_CPLL}	Total Jitter ⁽³⁾⁽⁴⁾	6.6 Gb/s	–	–	0.30	UI
DJ _{6.6_CPLL}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
TJ _{5.0}	Total Jitter ⁽³⁾⁽⁴⁾	5.0 Gb/s	–	–	0.30	UI
DJ _{5.0}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
TJ _{4.25}	Total Jitter ⁽³⁾⁽⁴⁾	4.25 Gb/s	–	–	0.30	UI
DJ _{4.25}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
TJ _{3.75}	Total Jitter ⁽³⁾⁽⁴⁾	3.75 Gb/s	–	–	0.30	UI
DJ _{3.75}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
TJ _{3.2}	Total Jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁵⁾	–	–	0.2	UI
DJ _{3.2}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.1	UI
TJ _{3.2L}	Total Jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁶⁾	–	–	0.32	UI
DJ _{3.2L}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.16	UI
TJ _{2.5}	Total Jitter ⁽³⁾⁽⁴⁾	2.5 Gb/s ⁽⁷⁾	–	–	0.20	UI
DJ _{2.5}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.08	UI
TJ _{1.25}	Total Jitter ⁽³⁾⁽⁴⁾	1.25 Gb/s ⁽⁸⁾	–	–	0.15	UI
DJ _{1.25}	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.06	UI
TJ ₅₀₀	Total Jitter ⁽³⁾⁽⁴⁾	500 Mb/s	–	–	0.1	UI
DJ ₅₀₀	Deterministic Jitter ⁽³⁾⁽⁴⁾		–	–	0.03	UI

Notes:

- Using same REFCLK input with TX phase alignment enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
- Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- All jitter values are based on a bit-error ratio of $1e^{-12}$.
- CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
- CPLL frequency at 1.6 GHz and TXOUT_DIV = 1.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.

Date	Version	Description
07/25/12	1.6	Updated the descriptions, changed V_{IN} and Note 2 and added Note 4 in Table 1. In Table 2, changed descriptions and notes, removed Note 7, changed GTX transceiver parameters and values and added Note 9. Updated parameters in Table 3. Added Table 4 and Table 5. Changed the typical values for many of the devices in Table 7. Updated LVCMOS12 and the SSTLs in Table 9. Updated many of the specifications in Table 10 and Table 11. Updated speed specification to v1.06 (-3, -2, -2L(1.0V), -1) and v1.05 (-2L(0.9V)) with appropriate changes to Table 14 and Table 15 including production release of the XC7K325T and the XC7K410T in the -2, -2L(1.0V), and -1 speed designations. Added notes and specifications to Table 17 and Table 18. Updated the IOB Pad Input/Output/3-State discussion and changed Table 21 by adding $T_{IOIBUFDISABLE}$. Removed many of the combinatorial delay specifications and T_{CINCK}/T_{CKCIN} from Table 28. Rearranged Table 51 including moving some parameters to Table 1. Added Table 56. Updated Table 57. In Table 59, updated SJ Jitter Tolerance with Stressed Eye section, page 51 and Note 8. Added Note 1, Note 2, and Note 3 to Table 62. Added Note 1 and Note 2 to Table 63, and line rate ranges. Updated Table 64 including adding Note 1. Updated Table 65 including adding Note 1. In Table 67 updated Note 1 and added Note 4. In Table 68, updated T_{POR} and F_{EMCCK}.
09/04/12	1.7	Updated Table 14 and Table 15 for production release of the XC7K160T in the -2, -2L(1.0V), and -1 speed designations.
09/26/12	1.8	In Table 2 , revised V_{CCINT} and V_{CCBRAM} and added Note 2 . Updated Table 14 and Table 15 for production release of the XC7K480T in the -2, -2L(1.0V), and -1 speed designations and the XC7K325T and XC7K410T in the -3 speed designation.
10/10/12	1.9	Updated the $I_{CCINTMIN}$ value for the XC7K355T in Table 7 . Updated Table 14 and Table 15 for production release of the XC7K420T in the -2, -2L(1.0V), and -1 speed designations.
10/25/12	2.0	Updated the AC Switching Characteristics based upon ISE 14.3 v1.07 for the -3, -2, -2L (1.0V), -1 speed specifications, and ISE 14.3 v1.06 for the -2L (0.9V) speed specifications throughout the document. Updated Table 14 and Table 15 for production release of the XC7K355T in the -2, -2L(1.0V), and -1 speed designations. Also updated Table 14 and Table 15 for production release of the XC7K325T and XC7K410T in the -2L (0.9V). Added values for Table 16 -2L (0.9V). Added package skew values to Table 50. In Table 53, increased -1 speed grade (FF package) F_{GTMAX} value from 6.6 Gb/s to 8.0 Gb/s.
10/31/12	2.1	Updated Table 14 and Table 15 for production release of the XC7K70T in the -2, -2L(1.0V), and -1 speed designations.
11/26/12	2.2	Updated Table 14 and Table 15 for production release of -3 speed designation for XC7K70T, XC7K160T, XC7K355T, XC7K420T, and XC7K480T. Removed Note 4 from Table 67 .
12/05/12	2.3	Updated Table 14 and Table 15 for production release of the -2L (0.9V) speed designation for XC7K160T, XC7K420T, and XC7K480T. Updated Note 1 in Table 50 .
12/12/12	2.4	Updated Table 14 and Table 15 for production release of the -2L (0.9V) speed designation for XC7K70T and XC7K355T. Added Internal Configuration Access Port section to Table 68 .

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